

wafer stack;

a measuring device for determining X-Y-positions of the thickness peaks (12) by measuring local thicknesses of the wafer stack (1) at a plurality of different X-Y-positions,

wherein the local thickness peaks (12) are equalized in a controlled manner by the at least one application unit (9, 9', 9'', 9''', 9^{IV}, 9^V, 9^{VI}),

wherein the product wafer (4) is disposed to local deformations by the at least one application unit (9, 9', 9'', 9''', 9^{IV}, 9^V, 9^{VI}) applying the local mechanical pressure, and

wherein the at least one application unit (9, 9', 9'', 9''', 9^{IV}, 9^V, 9^{VI}) applies the local mechanical pressure to the surface of the product wafer (4).

16. The device as claimed in claim 15, wherein the application apparatus (11, 11', 11'') comprises a plurality of the application units (9, 9', 9'', 9''', 9^{IV}, 9^V, 9^{VI}).

17. The device as claimed in one of claims 15 to 16, wherein the application apparatus (11, 11', 11'') comprises a membrane (14), which covers the at least one application unit (9, 9', 9'', 9''', 9^{IV}, 9^V, 9^{VI}).

18. The device as claimed in claim 15, wherein X-Y-positions of the local thickness peaks (12) are determined optically.

19. The device as claimed in claim 15, wherein X-Y-positions of the local thickness peaks (12) are determined acoustically.

20. The device as claimed in claim 16, wherein the plurality of the application units (9, 9', 9'', 9''', 9^{IV}, 9^V, 9^{VI}) are triggered separately.

21. The device as claimed in claim 16, wherein the plurality of the application units (9, 9', 9'', 9''', 9^{IV}, 9^V, 9^{VI}) are arranged discretely.